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# TMC2340

## Digital Synthesizer

Dual 16-Bit, 25 MOPS

### Description

The TMC2340 performs waveform synthesis, modulation, and demodulation. When presented with a TTL clock signal and user-selected 15-bit amplitude and 32-bit phase increment values, the TMC2340 automatically generates quadrature-matched pairs of 16-bit sine and cosine waves in DAC-compatible 16-bit offset binary format. If desired, these waveforms are easily phase or frequency-modulated on-chip, and the amplitude input facilitates gain adjustment or amplitude modulation. Digital output frequencies are restricted only by the Nyquist limit of clock rate/2, with frequency resolution of 0.006 Hz at the guaranteed maximum 25 MHz clock rate.

A new data word pair is available at the output every clock cycle. All input and output data ports are registered, with a user-configurable phase accumulator structure and input clock enables to simplify interfacing. The phase data range over a full  $2\pi$  radians. All signals are TTL compatible.

Fabricated in Raytheon Semiconductor's OMICRON-CTM one-micron CMOS process, the TMC2340 operates at the 25 MHz maximum clock rate over the full commercial temperature (0 to 70°C) and supply (4.75 to 5.25V) voltage ranges, and is available in a low-cost 120 pin plastic pin grid array. The MIL-STD-883 version, the TMC2340L5V, is housed in a ceramic chip carrier and is specified over the full extended (-55°C to 125°C) case temperature range.

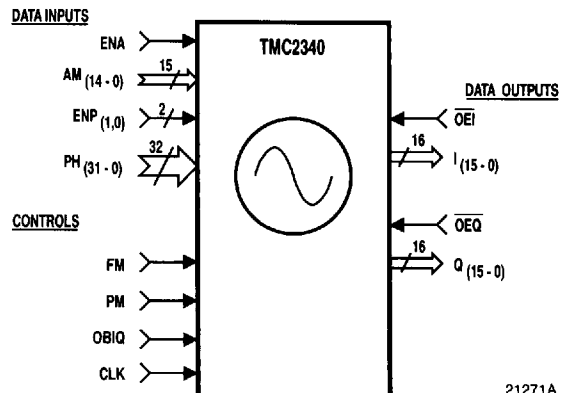
### Features

- ◆ User-configurable phase accumulator for waveform synthesis, frequency modulation or phase modulation
- ◆ Amplitude input for gain adjustment and amplitude modulation
- ◆ Guaranteed 25 Msps pipelined data throughput rate
- ◆ 15-bit magnitude, 32-bit phase data input precision
- ◆ 16-bit offset binary or 15-bit unsigned magnitude output data format
- ◆ Input register clock enables simplify interfacing
- ◆ Low power consumption CMOS process
- ◆ Single +5V power supply
- ◆ Available in a 120-pin plastic pin grid array package
- ◆ Compliant with MIL-STD-883B in a 132-leaded CERQUAD

### Applications

- ◆ Digital waveform synthesis, including quadrature functions
- ◆ Digital modulation and demodulation

### TMC2340 Logic Symbol



Signal Synthesis



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**Inputs/Outputs**

- AM<sub>14-0</sub> AM<sub>14-0</sub> is the registered peak amplitude 15-bit input data port. AM<sub>14</sub> is the MSB.
- PH<sub>31-0</sub> PH<sub>31-0</sub> is the registered Phase angle increment 32-bit input data port. The input phase accumulators are fed through this port in conjunction with the input enable select ENP<sub>1, 0</sub>. PH<sub>31</sub> is the MSB.
- I<sub>15-0</sub> I<sub>15-0</sub> is the registered X-coordinate 16-bit output data port. This output is forced into the high-impedance state when  $\overline{OEI}$ =HIGH. I<sub>0</sub> is the LSB. I<sub>15</sub> will be "stuck at" logic HIGH if OBIQ=0.
- Q<sub>15-0</sub> Q<sub>15-0</sub> is the registered Cartesian Y-coordinate 16-bit output data port. This output is forced to the high-impedance state when  $\overline{OEQ}$ =HIGH. Q<sub>0</sub> is the LSB. Q<sub>15</sub> will remain at logic HIGH if OBIQ=0.

**Controls**

- ENA Data presented to the input port AM are latched into the input registers on the current clock when ENA is HIGH. When ENA is LOW, the data stored in the register remains unchanged.
- ENP<sub>1, 0</sub> The value presented to the PH input port is latched into the phase accumulator input registers on the current clock, as determined by the control inputs ENP<sub>1, 0</sub>, as shown below:

ENP <sub>1,0</sub>	Instruction
00	No registers enabled, current data held
01	M register input enabled, C data held
10	C register input enabled, M data held
11	M register set to 0, C register input enabled

where C is the Carrier register and M is the Modulation register, and 0=LOW, 1=HIGH. See the *Functional Block Diagram*.

FM, PM The user determines the internal phase Accumulator structure implemented on the next clock by setting the accumulator control word FM, PM, as shown below:

FM, PM	Instruction
00	No accumulation performed
01	PM accumulator path enabled
10	FM accumulator path enabled
11	(Nonsensical) logical OR of PM and FM

where 0=LOW, 1=HIGH. See the *Functional Block Diagram*.

The accumulator will roll over correctly when full-scale is exceeded, allowing the user to perform continuous phase accumulation through  $2\pi$  radians, or 360 degrees.

OBIQ The format select control sets the numeric format of the Rectangular data: offset binary format when HIGH, and unsigned when LOW. This is a static input. See the *Timing Diagram*.

$\overline{OEI}$ ,  $\overline{OEQ}$  Data in the output registers are available at the outputs of the device when the respective asynchronous Output Enables are LOW. When  $\overline{OEX}$  or  $\overline{OEY}$  is HIGH, the respective output port is in the high-impedance state.

Signal Synthesis

### Package Interconnections

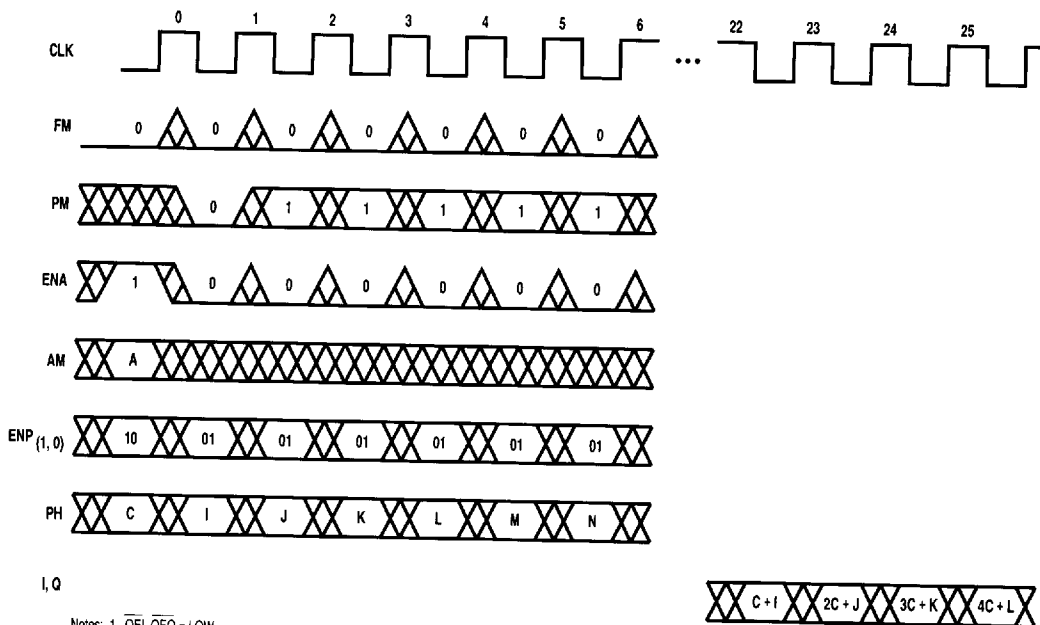
Signal Type	Signal Name	Function	H5 Package Pins	L5 Package Pins
Power	V <sub>DD</sub>	Supply Voltage	C3, E3, H3, L4, L6, L8, L11, F11, E11, C11, C8, C6	1, 9, 21, 37, 45, 53, 67, 87, 91, 99, 112, 120
	GND	Ground	D3, E2, E1, F2, G3, K3, L3, L7, K11, J11, G11, F12, E12, D11, C10, C9, B7, C7, C5, C4	5, 11, 12, 14, 17, 29, 33, 49, 75, 83, 86, 89, 95, 104, 108, 115, 116, 124, 129
Clock	CLK	System Clock	F3	13
Inputs	AM <sub>14-0</sub>	Radius Data	F13, G13, G12, H13, H12, H11, J13, J12, K13, K12, L13, L12, M13, M12, N13	85, 84, 82, 81, 80, 79, 78, 77, 76, 74, 73, 71, 69, 68, 66
	PH <sub>31-0</sub>	Phase Data	L10, N12, N11, M10, L9, N10, M9, N9, M8, N8, N7, M7, N6, M6, N5, M5, N4, L5, M4, N3, M3, N2, M2, N1, L2, M1, L1, K2, J3, K1, J2, J1	61, 60, 59, 58, 57, 56, 55, 54, 52, 51, 50, 48, 47, 46, 44, 43, 42, 41, 40, 39, 38, 36, 34, 31, 30, 28, 27, 26, 25, 24, 23, 22
Outputs	I <sub>15-0</sub>	I Data	D13, D12, C13, B13, C12, A13, B12, A12, B11, A11, B10, A10, B9, A9, B8, A8	90, 92, 93, 94, 96, 97, 100, 102, 105, 106, 107, 109, 110, 111, 113, 114
	Q <sub>15-0</sub>	Q Data	A7, A6, B6, A5, B5, A4, B4, A3, A2, B3, A1, B2, B1, C2, C1, D2	117, 118, 119, 121, 122, 123, 125, 126, 127, 130, 132, 3, 4, 6, 7, 8
Controls	ENR	Radius In Enable	M11	63
	ENP <sub>1,0</sub>	Phase In Enable	G1, G2	18, 16
	FM, PM	Modulation	H2, H1	20, 19
	OBIQ	Cartesian Data Format	F1	15
	OEI	I Out Enable	E13	88
	OEQ	Q Out Enable	D1	10
No Connect	NC	No Connect Pins	-	2, 32, 35, 62, 64, 65, 72, 98, 101, 103, 128, 131
		Index Pin	D4	-

### Static Control Input

OBIQ determines the numeric format of the output data: offset binary if HIGH and unsigned magnitude if LOW. This control acts with 2-cycle latency on the chip's 22-cycle data path and is normally hardwired to a system-specific state.



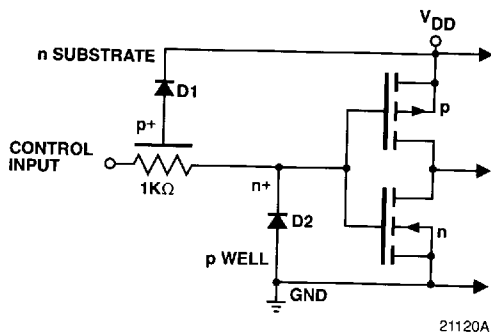
Figure 2. Timing Diagram, Phase Modulation



- Notes:
1. OEI, OEQ = LOW.
  2. Carrier C and peak amplitude A loaded on CLK 0.
  3. Modulation values I, J, K, L, ... loaded on CLK 1, CLK 2, etc.
  4. Output corresponding to modulation loaded at CLK I emerged  $t_{PD}$  after CLK I + 21.
  5. To modulate amplitude, vary AM with ENA = 1.

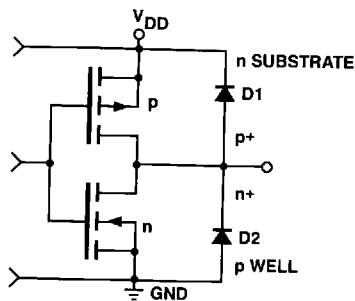
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Figure 3. Equivalent Input Circuit



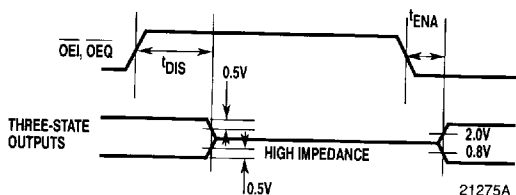
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Figure 4. Equivalent Output Circuit



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Figure 5. Transition Levels for Three-State Measurements



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**Absolute maximum ratings** (beyond which the device may be damaged) <sup>1</sup>

<b>Supply Voltage</b> .....	-0.5 to +7.0V
<b>Input Voltage</b> .....	-0.5 to (V <sub>DD</sub> +0.5)V
<b>Output Voltage</b>	
Applied voltage .....	-0.5 to (V <sub>DD</sub> +0.5)V <sup>2</sup>
Forced current .....	-6.0 to 6.0mA <sup>3,4</sup>
Short-circuit duration (single output in HIGH state to ground) .....	1 Second
<b>Temperature</b>	
Operating, case .....	-60 to +130°C
junction .....	175°C
Lead, soldering (10 seconds) .....	300°C
Storage .....	-65 to +150°C

- Notes:
1. Absolute maximum ratings are limiting values applied individually while all other parameters are within specified operating conditions. Functional operation under any of these conditions is NOT implied.
  2. Applied voltage must be current limited to specified range, and measured with respect to GND.
  3. Forcing voltage must be limited to specified range.
  4. Current is specified as conventional current flowing into the device.

**Operating conditions**

Parameter	Test Conditions	Temperature Range				Units
		Standard		Extended		
		Min	Max	Min	Max	
V <sub>DD</sub> Supply Voltage		4.75	5.25	4.5	5.5	V
V <sub>IL</sub> Input Voltage, Logic LOW			0.8		0.8	V
V <sub>IH</sub> Input Voltage, Logic HIGH		2.0		2.0		V
I <sub>OL</sub> Output Current, Logic LOW			8.0		8.0	mA
I <sub>OH</sub> Output Current, Logic HIGH			-4.0		-4.0	mA
t <sub>CY</sub> Cycle Time	V <sub>DD</sub> =Min TMC2340-1		50		55	ns
			40		45	ns
t <sub>PWL</sub> Clock Pulse Width, LOW	V <sub>DD</sub> =Min TMC2340-1	10		11		ns
		8		8		ns
t <sub>PWH</sub> Clock Pulse Width, HIGH	V <sub>DD</sub> =Min TMC2340-1	8		8		ns
		6		6		ns
t <sub>S</sub> Input Setup Time	TMC2340-1	12		13		ns
		10		11		ns
t <sub>H</sub> Input Hold Time	TMC2340-1	1		2		ns
		1		2		ns
T <sub>A</sub> Ambient Temperature, Still Air		0	70			°C
T <sub>C</sub> Case Temperature				-55	125	°C

### Electrical characteristics within specified operating conditions <sup>1</sup>

Parameter	Test Conditions	Temperature Range				Units
		Standard		Extended		
		Min	Max	Min	Max	
I <sub>DDQ</sub> Supply Current, Quiescent	V <sub>DD</sub> = Max, V <sub>IN</sub> = 0V		10		10	mA
I <sub>DDU</sub> Supply Current, Unloaded	V <sub>DD</sub> = Max, f = 20MHz OE $\bar{E}$ and OE $\bar{E}$ = V <sub>DD</sub>		160		160	mA
I <sub>IL</sub> Input Current, Logic LOW	V <sub>DD</sub> = Max, V <sub>IN</sub> = 0V		-10		-10	$\mu$ A
I <sub>IH</sub> Input Current, Logic HIGH	V <sub>DD</sub> = Max, V <sub>IN</sub> = V <sub>DD</sub>		10		10	$\mu$ A
V <sub>OL</sub> Output Voltage, Logic LOW	V <sub>DD</sub> = Min, I <sub>OL</sub> = Max		0.4		0.4	V
V <sub>OH</sub> Output Voltage, Logic HIGH	V <sub>DD</sub> = Min, I <sub>OH</sub> = Max	2.4		2.4		V
I <sub>OZL</sub> Hi-Z Output Leakage Current, Output LOW	V <sub>DD</sub> = Max, V <sub>IN</sub> = 0V		-40		-40	$\mu$ A
I <sub>OZH</sub> Hi-Z Output Leakage Current, Output HIGH	V <sub>DD</sub> = Max, V <sub>IN</sub> = V <sub>DD</sub>		40		40	$\mu$ A
I <sub>OS</sub> Short-Circuit Output Current	V <sub>DD</sub> = Max, Output HIGH, one pin to ground, one second duration max.	-20	-100	-20	-100	$\mu$ A
C <sub>I</sub> Input Capacitance	T <sub>A</sub> = 25°C, f = 1MHz		10		10	pF
C <sub>O</sub> Output Capacitance	T <sub>A</sub> = 25°C, f = 1MHz		10		10	pF

Note: 1. Actual test conditions may vary from those shown, but specified operation is guaranteed.

### Switching characteristics within specified operating conditions

Parameter	Test Conditions	Temperature Range				Units
		Standard		Extended		
		Min	Max	Min	Max	
t <sub>D</sub> Output Delay	V <sub>DD</sub> = Min, C <sub>LOAD</sub> = 40pF		22		25	ns
	TMC2340-1		20		23	ns
t <sub>HO</sub> Output Hold Time	V <sub>DD</sub> = Max, C <sub>LOAD</sub> = 40pF		4		4	ns
	TMC2340-1		4		4	ns
t <sub>ENA</sub> Output Enable Delay	V <sub>DD</sub> = Min, C <sub>LOAD</sub> = 40pF		13		17	ns
	TMC2340-1		12		15	ns
t <sub>DIS</sub> Output Disable Delay	V <sub>DD</sub> = Min, C <sub>LOAD</sub> = 40pF		14		14	ns
	TMC2340-1		13		13	ns



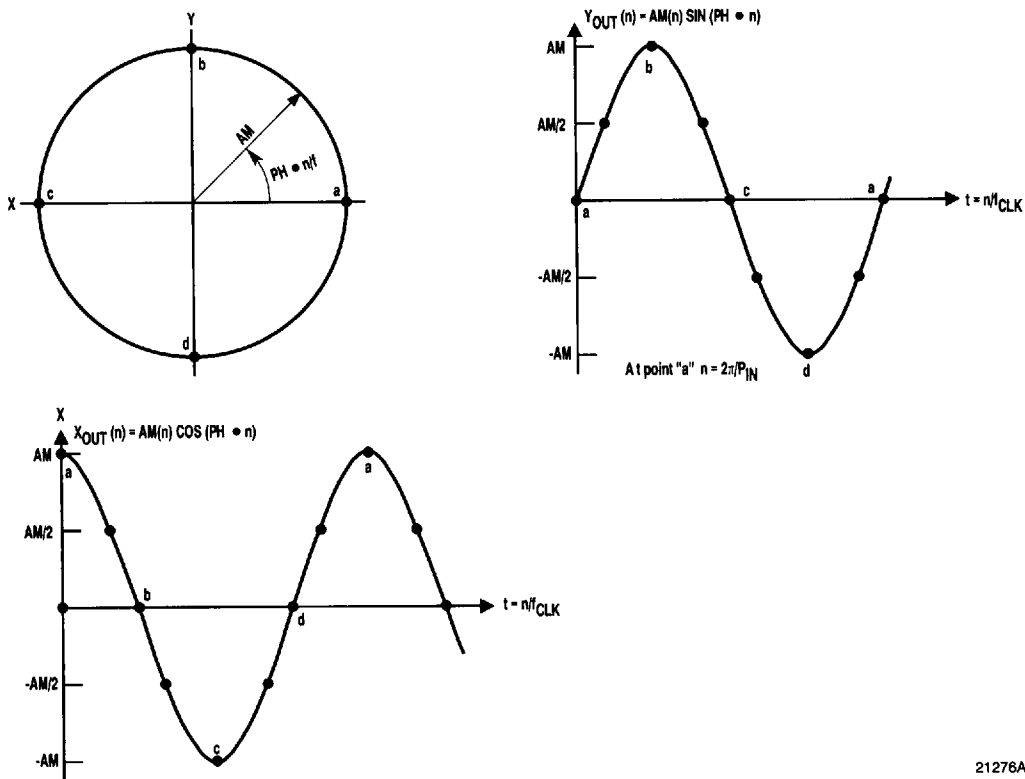
### Phase/Amplitude to Sine/Cosine Conversion Geometry

#### Polar-To-Rectangular Conversion Geometry

The TMC2340 performs a coordinate-space transformation according to the familiar trigonometric relationships shown in *Figure 6*.

With constant amplitude and phase increment values and either FM or PM HIGH, the TMC2340 will output a series of complex number pairs representing the horizontal and vertical projections of a vector rotating about the origin, i.e., a cosine wave and a sine wave.

**Figure 6. Input to Output Relationship for Sinusoid Generation**



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## Digital Waveform Synthesis

### Waveform Generation and Modulation

Utilizing the internal phase accumulators in a TMC2340, users can easily generate high-accuracy digital quadrature sinusoidal waveforms with minimal support. The 32-bit data path ensures negligible cumulative error in most applications, and the accuracy of the transform is limited only by the truncation of the result to 16 bits prior to the Transform Processor and the  $\pm 1$  LSB maximum error of the transform algorithm. Amplitude Modulation is of course performed simply by varying the amplitude input. Either Frequency (phase angle shifted by the cumulative sum of the modulation input) or Phase (phase angle shifted by the instantaneous modulation input) Modulation can be realized by configuring the TMC2340 as shown in *Figures 7 and 8*.

In *Figure 7*, the output valid during clock rising edge  $m+22$  is:

$$I_{m+22} = AM_m \cos(PH_m + mPC)$$

$$Q_{m+22} = AM_m \sin(PH_m + mPC)$$

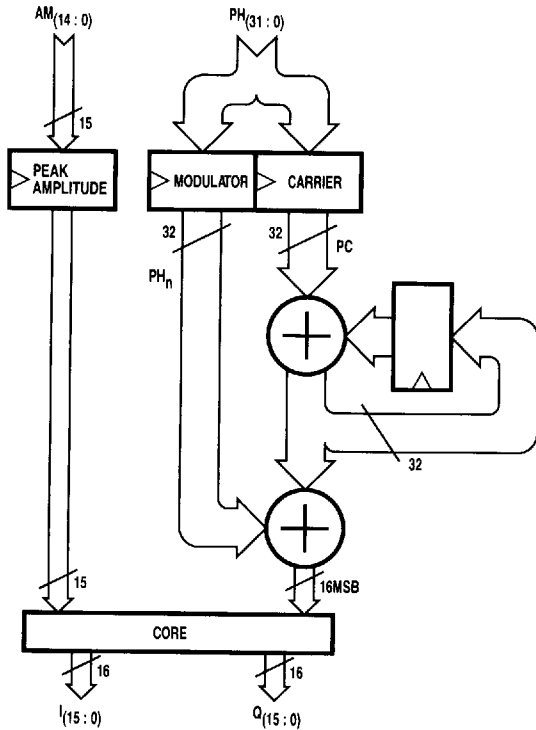
where  $PH_m$  and  $AM_m$  are the chip inputs at rising edge  $m$ ,  $PC$  is the (constant) carrier phase increment,  $PM_1=0$ ,  $PM_{2...m}=1$ , and  $FM_{1-m}=0$ .

Expressed in terms of time instead of clock cycles,

$$I_{(m+22)/f_{clk}} = AM_m / f_{clk} \cos(PH_m / f_{clk})$$

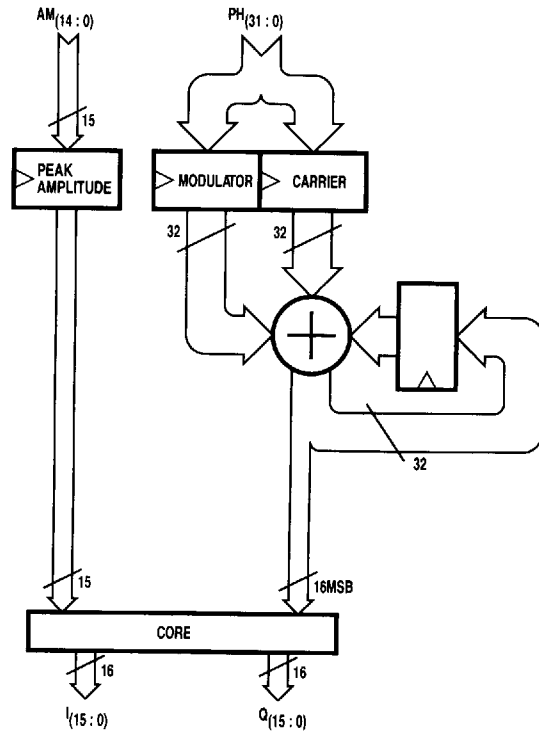
where  $f_{clk}$  is the frequency of the square wave applied to CLK.

**Figure 7. Performing Phase Modulation**



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**Figure 8. Performing Frequency Modulation**



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In *Figure 8*, the output valid during clock rising edge  $n+22$  is:

$$I_{m+22} = AM_m \cos \left( \sum_{m=1}^n PH_m + nPC \right)$$

$$Q_{n+22} = AM_m \sin \left( \sum_{m=1}^n PH_m + nPC \right)$$

where  $PH_m$  and  $AM_m$  are the chip inputs at rising edge  $m$ ,  $PC$  is the (constant) carrier phase increment,  $FM_1=0, FM_2...n=1$ , and  $PM=0$ .

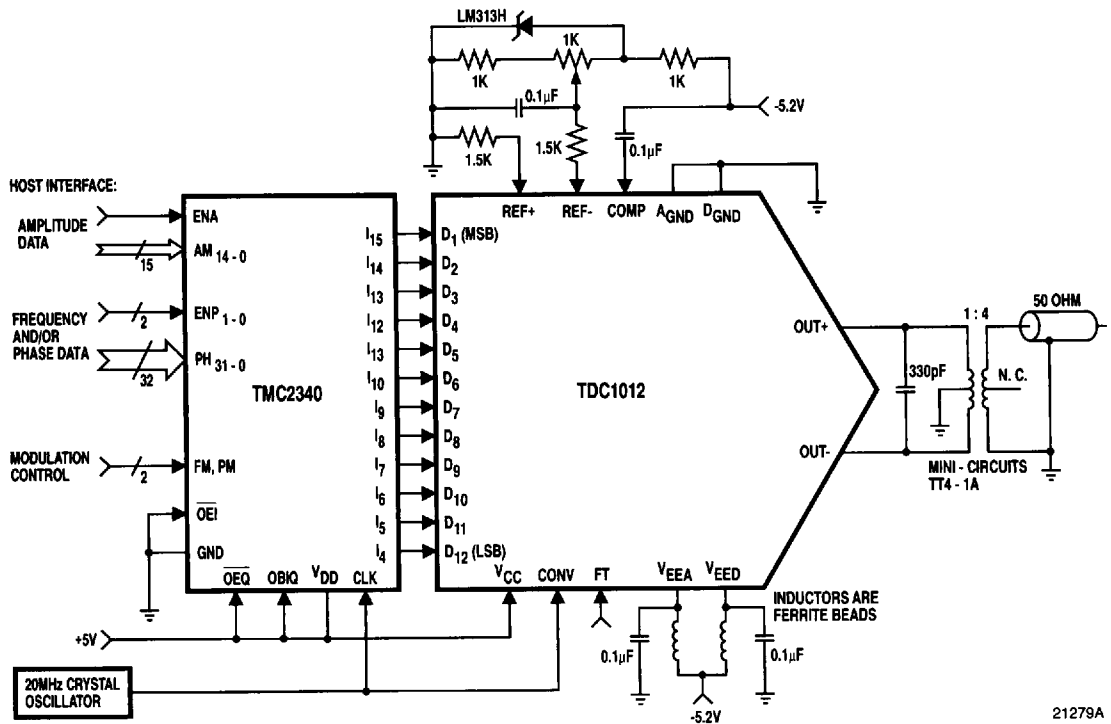
Expressed in terms of time instead of clock cycles,

$$I_{[n+22]/fclk} = AM_m/fclk \cos \left( \sum_{m=1}^n PH_m/fclk + PC \cdot m/fclk \right)$$

**Digital Synthesizer with TDC1012 D/A Converter**

Connection of the TMC2340 to the TDC1012 D/A converter is straightforward. As shown in *Figure 9*, the TDC1012 data lines are connected to either the I or Q outputs. Both outputs may be used, with two TDC1012's for quadrature synthesis.

**Figure 9. Frequency Synthesizer**



Note: To use two TDC1012's in quadrature, connect second TDC1012 to  $Q_{15}$  (MSB) to  $Q_4$  and ground  $\overline{OEQ}$ .

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## Control of the TMC2340

The TMC2340 needs to be initialized to tell it what frequency and amplitude sinusoid to generate. To initialize amplitude, apply the desired full-scale amplitude to the AM input port of the TMC2340 (AM<sub>14</sub> through AM<sub>0</sub>) and pull ENA HIGH for one clock cycle. This will load the amplitude. If ENA is held HIGH, then the amplitude will follow the inputs on the AM port. If the user assumes an implied binary point before the MSB of the AM port, the input range will be 0 to just under 1, and the outputs will fall between 0 and 2, with binary points after I<sub>15</sub> and Q<sub>15</sub>.

To set the frequency, the C register must be loaded with a value which is the phase increment per clock cycle. If the binary point is considered to be just left of the MSB (input range is 0 to almost 1) then the output frequency is the TMC2340 clock frequency multiplied by the number loaded into C. Since C is 32 bits wide, with a 20MHz clock, one LSB represents a frequency increment of 0.005Hz.

To load the C register, set ENYP<sub>1</sub>=1 and ENYP<sub>0</sub>=0; the data presented at the PH port will be loaded on the next clock rising edge.

At this point the TMC2340 has been initialized and can be put into one of three modes depending upon the states of FM and PM:

Mode 0 FM=0, PM=0

In this mode the chip is in standby. The unchanging output corresponds to AM cos(PM) on the I outputs with PM being the phase increment.

Mode 1 FM=1, PM=0

Frequency Modulation Mode. The chip generates an output signal of peak amplitude AM and frequency determined by accumulating the sum of the phase

increment values in the C and M registers (more about the M register in a later section).

Mode 2 FM=0, PM=1

Phase Modulation Mode. The TMC2340 generates a sinusoid of the frequency represented in the C register and the peak amplitude in the AM register. On each clock cycle, the phase of the signal is offset by the value in the M register.

## Modulation

The output of the TMC2340 can be phase (Mode 2) or frequency (Mode 1) modulated. An unmodulated sinusoid results if the contents of registers C and M are held constant. Its frequency is set by C (Mode 2) or C+M (Mode 1). Since the state of the M register is not defined at power up, the M register should be loaded or cleared to begin operation.

If the signal is to be frequency modulated then the modulation signal is loaded into the M register. The format for the frequency is the same as that for the C register. If ENYP<sub>1</sub><sub>0</sub>=0, 1 then the data that is presented at the PH port is automatically loaded on each clock rising edge.

For phase modulation, the phase deviation is loaded into the M register (same manner as for frequency modulation). The units of the phase offset are cycles and full-scale is just under one output cycle per TMC2340 clock cycle. The MSB represents a phase of 180°, and the LSB a phase of about  $8 \times 10^{-8}$  degrees (eight one-hundred-millionths of a degree), or  $\pi/2^{31}$  radians.

To synchronize two TMC2340s, first load them with their respective data in mode 0, then switch them simultaneously to either Mode 1 or Mode 2.

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**Calculating Frequency, Amplitude, and Phase Input Values for the TMC2340**

This Application Brief discusses equations which simplify the calculation of register values which control the TMC2340. These values allow the generation of output carrier frequency, frequency or phase modulation, and output amplitude.

The results of the equations are converted to binary register values and should be rounded to the resolution of the applicable register (32 or 15-bits). For negative values of phase or frequency modulation, use these equations for positive values and see Table 1 of the TMC2340 data sheet to convert them to negative values.

The TMC2340 operates by continuously incrementing a register (phase accumulator) that rolls over when it becomes full. For example, if the next increment to the phase accumulator causes it to overflow by 47 LSBs, the phase accumulator retains the value 47. The value present in the carrier register (C) is the amount by which the phase accumulator is incremented each system clock cycle. As the value of the carrier register is increased, the value with which the the phase accumulator is incremented each clock cycle is increased, resulting in an increased carrier frequency.

**CARRIER FREQUENCY:**

$$\text{Carrier Register (C) Value} = \frac{\text{Desired Carrier Frequency}}{\text{Clock Frequency}} \times 2^{32}$$

**AMPLITUDE AND AMPLITUDE MODULATION:**

$$\text{AM Register Value} = \frac{\text{Desired Output Amplitude}}{\text{Full-Scale Output Amplitude}} \times (2^{15} - 1)$$

**FREQUENCY MODULATION:**

$$\text{Modulation Register (M) Value} = \frac{\text{Desired Change in Carrier Frequency}}{\text{Clock Frequency}} \times 2^{32}$$

The magnitude of the carrier is determined or modulated by the value loaded in the AM register. Phase modulation is accomplished by adding the value of the phase accumulator to the value of the modulation (M) register. This adds an offset to the phase of the carrier. This does not affect the increment value of the phase accumulator and therefore only effects the phase of the carrier, leaving the frequency constant.

Adding the value of the modulation register to the phase accumulator along with the value of the carrier register on each clock cycle results in a shift in frequency. This is because the phase accumulator is incremented by a different amount each clock cycle.

Frequency or phase modulation is selected with the FM and PM input pins which configure the TMC2340. The equations presented herein are useful for setting carrier frequency and phase, output amplitude, and frequency and phase modulation. To modulate the carrier with an external signal, the signal must be digitized and those values loaded into the modulation inputs of the TMC2340.

The carrier and modulation registers are loaded through the PH<sub>31-0</sub> inputs. The ENP<sub>1,0</sub> inputs select the desired register. The amplitude register is loaded through the AM<sub>14-0</sub> inputs.

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**PHASE MODULATION:**

$$\text{Modulation Register (M) Value} = \frac{\text{Desired Change in Phase in radians (degrees)}}{2\pi (360^\circ)} \times 2^{32}$$

**EXAMPLE 1: Set carrier frequency to 3.579545 MHz with a system clock of 20MHz.**

$$\text{Carrier Register (C) Value} = \frac{\text{Desired Carrier Frequency}}{\text{Clock Frequency}} \times 2^{32} = \frac{3.579545 \times 10^6}{20 \times 10^6} \times 2^{32}$$

$$C = 0.17897725 \times 4,294,967,296 = 768,701,436 = 2DD1\ 73FBh \\ = 0010\ 1101\ 1101\ 0001\ 0111\ 0011\ 1111\ 1011 = PH_{31-0}$$

**EXAMPLE 2: Set output amplitude to be 12.2% of full-scale.**

$$\text{AM Register Value} = \frac{\text{Desired Output Amplitude}}{\text{Full-Scale Output Amplitude}} \times (2^{15}-1) = \frac{0.122}{1.000} \times 32767$$

$$AM = 3,998 = 0F9Eh = 0001\ 1111\ 0011\ 1100 = AM_{14-0}$$

**EXAMPLE 3: Change carrier frequency by 10kHz with a system clock of 3 MHz.**

$$\text{Modulation Register (M) Value} = \frac{\text{Desired Change in Carrier Frequency}}{\text{Clock Frequency}} \times 2^{32}$$

$$M = \frac{10 \times 10^3}{3 \times 10^6} \times 2^{32} = 14,316,558 = 00DA\ 740Eh$$

$$M = 0000\ 0000\ 1101\ 1010\ 0111\ 0100\ 0000\ 1110 = PH_{31-0}$$

**EXAMPLE 4: Shift the phase of any carrier frequency by 12°.**

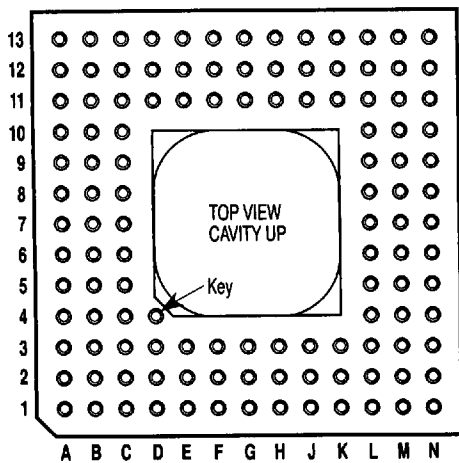
$$\text{Modulation Register (M) Value} = \frac{\text{Desired Change in Phase}}{360^\circ} \times 2^{32} = \frac{12}{360} \times 2^{32}$$

$$M = 0.033333 \times 2^{32} = 143,165,577 = 0888\ 8889h \\ = 0000\ 1000\ 1000\ 1000\ 1000\ 1000\ 1000\ 1001 = PH_{31-0}$$

RAYTHEON/ SEMICONDUCTOR

Pin Assignments — 121-Pin Plastic Pin Grid Array, H5 Package; 120-Pin Ceramic PGA, G1 Package

Pin	Name	Pin	Name	Pin	Name	Pin	Name	Pin	Name	Pin	Name	Pin	Name	Pin	Name
A1	Q <sub>5</sub>	B3	Q <sub>6</sub>	C5	GND	E1	GND	G11	GND	K1	PH <sub>2</sub>	L10	PH <sub>31</sub>	M12	AM <sub>1</sub>
A2	Q <sub>7</sub>	B4	Q <sub>9</sub>	C6	V <sub>DD</sub>	E2	GND	G12	AM <sub>12</sub>	K2	PH <sub>4</sub>	L11	V <sub>DD</sub>	M13	AM <sub>2</sub>
A3	Q <sub>8</sub>	B5	Q <sub>11</sub>	C7	GND	E3	V <sub>DD</sub>	G13	AM <sub>13</sub>	K3	GND	L12	AM <sub>3</sub>	N1	PH <sub>8</sub>
A4	Q <sub>10</sub>	B6	Q <sub>13</sub>	C8	V <sub>DD</sub>	E11	V <sub>DD</sub>	H1	PM	K11	GND	L13	AM <sub>4</sub>	N2	PH <sub>10</sub>
A5	Q <sub>12</sub>	B7	GND	C9	GND	E12	GND	H2	FM	K12	AM <sub>5</sub>	M1	PH <sub>6</sub>	N3	PH <sub>12</sub>
A6	Q <sub>14</sub>	B8	I <sub>1</sub>	C10	GND	E13	$\overline{OE}$	H3	V <sub>DD</sub>	K13	AM <sub>6</sub>	M2	PH <sub>9</sub>	N4	PH <sub>15</sub>
A7	Q <sub>15</sub>	B9	I <sub>3</sub>	C11	V <sub>DD</sub>	F1	OBIQ	H11	AM <sub>9</sub>	L1	PH <sub>5</sub>	M3	PH <sub>11</sub>	N5	PH <sub>17</sub>
A8	I <sub>0</sub>	B10	I <sub>5</sub>	C12	I <sub>11</sub>	F2	GND	H12	AM <sub>10</sub>	L2	PH <sub>7</sub>	M4	PH <sub>13</sub>	N6	PH <sub>19</sub>
A9	I <sub>2</sub>	B11	I <sub>7</sub>	C13	I <sub>13</sub>	F3	CLK	H13	AM <sub>11</sub>	L3	GND	M5	PH <sub>16</sub>	N7	PH <sub>21</sub>
A10	I <sub>4</sub>	B12	I <sub>9</sub>	D1	$\overline{OEQ}$	F11	V <sub>DD</sub>	J1	PH <sub>0</sub>	L4	V <sub>DD</sub>	M6	PH <sub>18</sub>	N8	PH <sub>22</sub>
A11	I <sub>6</sub>	B13	I <sub>12</sub>	D2	Q <sub>0</sub>	F12	GND	J2	PH <sub>1</sub>	L5	PH <sub>14</sub>	M7	PH <sub>20</sub>	N9	PH <sub>24</sub>
A12	I <sub>8</sub>	C1	Q <sub>1</sub>	D3	GND	F13	AM <sub>14</sub>	J3	PH <sub>3</sub>	L6	V <sub>DD</sub>	M8	PH <sub>23</sub>	N10	PH <sub>26</sub>
A13	I <sub>10</sub>	C2	Q <sub>2</sub>	D11	GND	G1	ENP <sub>1</sub>	J11	GND	L7	GND	M9	PH <sub>25</sub>	N11	PH <sub>29</sub>
B1	Q <sub>3</sub>	C3	V <sub>DD</sub>	D12	I <sub>14</sub>	G2	ENP <sub>0</sub>	J12	AM <sub>7</sub>	L8	V <sub>DD</sub>	M10	PH <sub>28</sub>	N12	PH <sub>30</sub>
B2	Q <sub>4</sub>	C4	GND	D13	I <sub>15</sub>	G3	GND	J13	AM <sub>8</sub>	L9	PH <sub>27</sub>	M11	ENA	N13	AM <sub>0</sub>

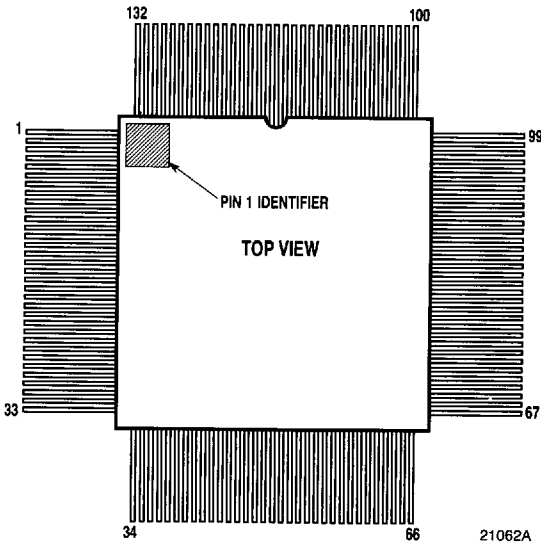


21041A

Signal Synthesis

### Pin Assignments — 132 Leaded CERQUAD, L5 Package

Pin	Name	Pin	Name	Pin	Name	Pin	Name	Pin	Name	Pin	Name
1	V <sub>DD</sub>	23	PH <sub>1</sub>	45	V <sub>DD</sub>	67	V <sub>DD</sub>	89	GND	111	I <sub>2</sub>
2	NC	24	PH <sub>2</sub>	46	PH <sub>18</sub>	68	AM <sub>1</sub>	90	I <sub>15</sub>	112	V <sub>DD</sub>
3	Q <sub>4</sub>	25	PH <sub>3</sub>	47	PH <sub>19</sub>	69	AM <sub>2</sub>	91	V <sub>DD</sub>	113	I <sub>1</sub>
4	Q <sub>3</sub>	26	PH <sub>4</sub>	48	PH <sub>20</sub>	70	GND	92	I <sub>14</sub>	114	I <sub>0</sub>
5	GND	27	PH <sub>5</sub>	49	GND	71	AM <sub>3</sub>	93	I <sub>13</sub>	115	GND
6	Q <sub>2</sub>	28	PH <sub>6</sub>	50	PH <sub>21</sub>	72	NC	94	I <sub>12</sub>	116	GND
7	Q <sub>1</sub>	29	GND	51	PH <sub>22</sub>	73	AM <sub>4</sub>	95	GND	117	Q <sub>15</sub>
8	Q <sub>0</sub>	30	PH <sub>7</sub>	52	PH <sub>23</sub>	74	AM <sub>5</sub>	96	I <sub>11</sub>	118	Q <sub>14</sub>
9	V <sub>DD</sub>	31	PH <sub>8</sub>	53	V <sub>DD</sub>	75	GND	97	I <sub>10</sub>	119	Q <sub>13</sub>
10	$\overline{OE}$	32	NC	54	PH <sub>24</sub>	76	AM <sub>6</sub>	98	NC	120	V <sub>DD</sub>
11	GND	33	GND	55	PH <sub>25</sub>	77	AM <sub>7</sub>	99	V <sub>DD</sub>	121	Q <sub>12</sub>
12	GND	34	PH <sub>9</sub>	56	PH <sub>26</sub>	78	AM <sub>8</sub>	100	I <sub>9</sub>	122	Q <sub>11</sub>
13	CLK	35	NC	57	PH <sub>27</sub>	79	AM <sub>9</sub>	101	NC	123	Q <sub>10</sub>
14	GND	36	PH <sub>10</sub>	58	PH <sub>28</sub>	80	AM <sub>10</sub>	102	I <sub>8</sub>	124	GND
15	OBIQ	37	V <sub>DD</sub>	59	PH <sub>29</sub>	81	AM <sub>11</sub>	103	NC	125	Q <sub>9</sub>
16	ENP <sub>0</sub>	38	PH <sub>11</sub>	60	PH <sub>30</sub>	82	AM <sub>12</sub>	104	GND	126	Q <sub>8</sub>
17	GND	39	PH <sub>12</sub>	61	PH <sub>31</sub>	83	GND	105	I <sub>7</sub>	127	Q <sub>7</sub>
18	ENP <sub>1</sub>	40	PH <sub>13</sub>	62	NC	84	AM <sub>13</sub>	106	I <sub>6</sub>	128	NC
19	PM	41	PH <sub>14</sub>	63	ENA	85	AM <sub>14</sub>	107	I <sub>5</sub>	129	GND
20	FM	42	PH <sub>15</sub>	64	NC	86	GND	108	GND	130	Q <sub>6</sub>
21	V <sub>DD</sub>	43	PH <sub>16</sub>	65	NC	87	V <sub>DD</sub>	109	I <sub>4</sub>	131	NC
22	PH <sub>0</sub>	44	PH <sub>17</sub>	66	AM <sub>0</sub>	88	$\overline{OE}$	110	I <sub>3</sub>	132	Q <sub>5</sub>



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RAYTHEON/ SEMICONDUCTOR

## Ordering Information

Product Number	Temperature Range	Screening	Package	Package Marking
TMC2340H5C1	STD: $T_A = 0$ to $70^\circ\text{C}$	Commercial	121-Pin Plastic Pin Grid Array	2340H5C1
TMC2340H5C	STD: $T_A = 0$ to $70^\circ\text{C}$	Commercial	121-Pin Plastic Pin Grid Array	2340H5C
TMC2340L5V1	EXT: $T_C = -55^\circ\text{C}$ to $125^\circ\text{C}$	MIL-STD-883B	132-Leaded CERQUAD	2340L5V1
TMC2340L5V	EXT: $T_C = -55^\circ\text{C}$ to $125^\circ\text{C}$	MIL-STD-883B	132-Leaded CERQUAD	2340L5V
TMC2340G1V1	EXT: $T_C = -55^\circ\text{C}$ to $125^\circ\text{C}$	MIL-STD-883B	120-Pin Ceramic PGA	2340G1V1
TMC2340G1V	EXT: $T_C = -55^\circ\text{C}$ to $125^\circ\text{C}$	MIL-STD-883B	120-Pin Ceramic PGA	2340G1V

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